

# High Voltage Rectifying Diode

## MD4DN11

● **Features**

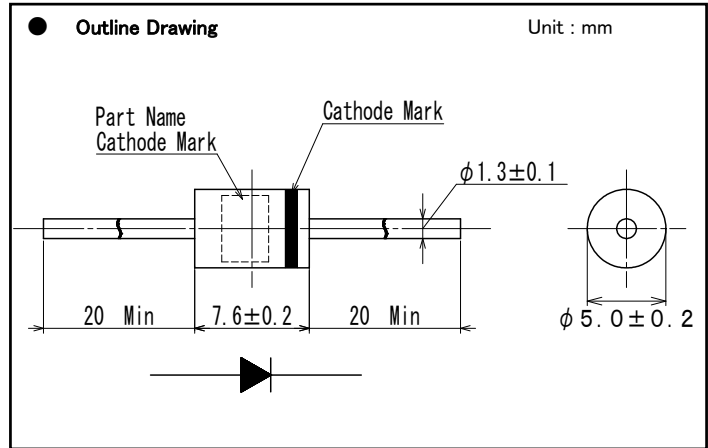
- VRM=4kV to 150kV
- Avalanche characteristics

● **Applications**

- General Purpose Rectifier

● **Structures**

- Resin molded, and diffused junction silicon diode.
- Part Name : [ 4N11 ]
- Weight : 1.15g
- Terminal plating : Sn
- Conforms to RoHS regulations



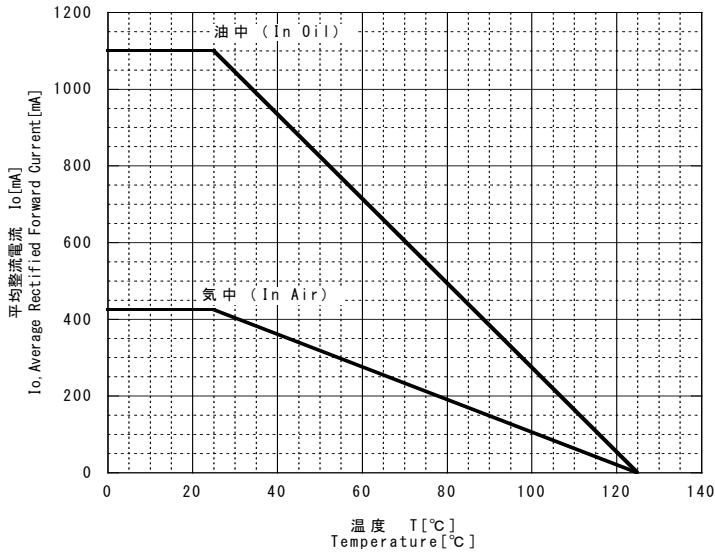
● **Absolute Maximum Ratings**

Items	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V <sub>RM</sub>	In Oil	4	kV
		In Air	4	
Average Rectified Forward Current	I <sub>O</sub>	In Oil To=25°C, 50Hz,Single-phase,Half sin Wave	1100	mA
		In Air Ta=25°C, 50Hz,Single-phase,Half sin Wave	475	
Peak Forward Surge Current	I <sub>SM</sub>	Ta=25°C, 50Hz,Half sin wave, Peak, Non-Repeative	50	A
Operating Junction Temperature	T <sub>j</sub>	—	-30~+125	°C
Storage Temperature	T <sub>stg</sub>	—	-30~+125	°C

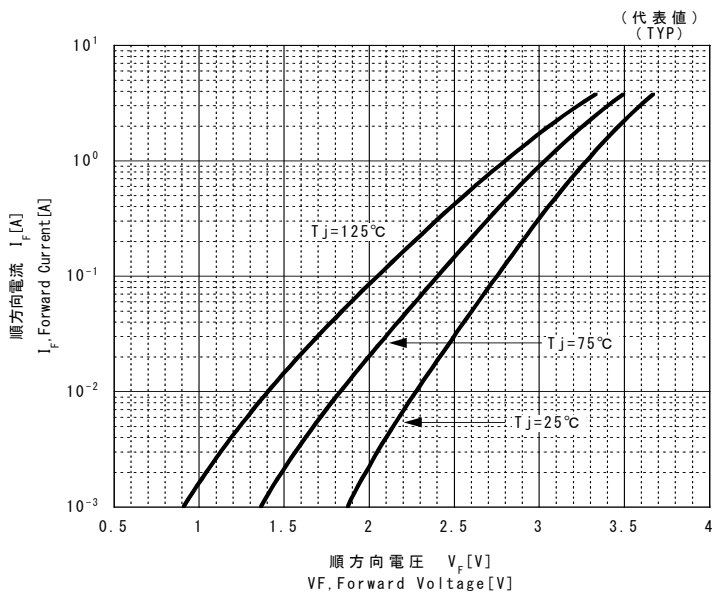
● **Electrical Characteristics (Ta=25°C)**

Items	Symbol	Conditions	MAX.	Unit
Forward Voltage Drop	V <sub>F</sub>	I <sub>F</sub> =1100mA	4	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> =3.2kV	50	μA

● Characteristics Diagrams



AVERAGE RECTIFIED FORWARD CURRENT



FORWARD CHARACTERISTICS